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Signature

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(to be used for all correspondence after initial filing)

PTO/SB/21 (08-00)

Application Number 09/832,844

Filing Date April 12, 2001

First Named Inventor Shunpei YAMAZAKI

Group Art Unit 2826

Examiner Name M. Tran

Attorney Docket Number 0756-2288

Total Number of Pages in This S	ubmission	Attorney Docket Number	er 0756-2288		
ENCLOSURES (check all that apply)					
Fee Transmittal Form Fee Attached Amendment / Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53			After Allowance Communication to Group Appeal Communication to Board of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter Other Enclosures 1. Request for Certificate of Correction and Form PTO1050 2. 3. 4. 5. 6.		
	SIGNATURE	E OF APPLICANT, ATTORNEY, C	DR AGENT		
Firm or Individual name	Robinson In PMB 955 21010 Sout	inson, Reg. No. 38,285 htellectual Property Law Office, hbank Street alls, VA 20165	P.C. Certificate MAY 2.9 2007 of Correction		
Signature	1.		Of College		
Date	May 22, 200	07			
		CERTIFICATE OF MAILING			
		g deposited with the United States Posi issioner for Patents, P.O. Box 1450, Ale	tal Service with sufficient postage as first exandria, VA 22313-1450 on the date		

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date

May 22, 2007

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TRANSMITTAL

Filing Date April 12, 2001 **FORM** First Named Inventor Shunpei YAMAZAKI **Group Art Unit** 2826 **Examiner Name** M. Tran (to be used for all correspondence after initial filing) Total Number of Pages in This Submission **Attorney Docket Number** 0756-2288

Application Number

PTO/SB/21 (08-00)

09/832,844

May 22, 2007

	· _ ·	ENCLOSURES (check all that apply)			
Fee Transmittal Form Fee Attached Amendment / Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53		Assignment Papers (for an Application) Drawing(s) Declaration and Power of Attorney Licensing-related Papers Petition Petition to Convert to a Provisional Application Power of Attorney, Revocation Change of Correspondence Address Terminal Disclaimer Request for Refund CD, Number of CD(s) Remarks After Allowance Communication to Group Appeal Communication to Board of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter Other Enclosures 1. Request for Certificate of Correction and Form PTO1050 2. 3. 4. 5. 6. Remarks The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 50- 2280 for the above identified docket number.			
	SIGNATU	JRE OF APPLICANT, ATTORNEY, OR AGENT			
Firm or Individual name Signature Date	Eric J. Robinson, Reg. No. 38,285 Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, VA 20165				
Date May 22, 2007					
		CERTIFICATE OF MAILING			
I hereby certify that this corresp class mail in an envelope addre indicated below.	ondence is be ssed to: Com	eing deposited with the United States Postal Service with sufficient postage as first nmissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the date			
Type or printed name Ade		le M. Stamper			
Signature		Add May 22 2007			

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Attorney Docket No. 0756-2288



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

The Patent Application of:) Group Art Unit: 2826	
Shunpei YAMAZAKI) Examiner: M. Tran	
Patent No.: 7,067,844) <u>CERTIFICATE OF MAILING</u> I hereby certify that this corresponde	nce i
Dated: June 27, 2006	being deposited with the United States Service with sufficient postage as Firs	Posta
Serial No. 09/832,844) Mail in an envelope addresse Commissioner for Patents, P.O. Box	ed to
Filed: April 12, 2001) Alexandria, VA 22313-1450, on May 22	2, 2007
For: ELECTRO-OPTICAL DEVICE	, add m Stamper	

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR § 1.322 FOR CORRECTION OF OFFICE MISTAKE

ATTN: Certificate of Correction Branch Honorable Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

As provided in detail in the attached, the patentee respectfully requests that a Certificate of Correction be granted in the above-identified patent to correct a mistake in a patent, incurred through the fault of the Office.

Under 37 CFR 1.322, "The Commissioner may issue a certificate of correction pursuant to 35 U.S.C. 254 to correct a mistake in a patent, incurred through the fault of the Office, which mistake is clearly disclosed in the records of the Office at the request of the patentee or the patentee's assignee."

The Patentee furthermore requests <u>Expedited Issuance</u> of this Certificate of Correction in accordance with MPEP § 1480.01. Specifically, this section provides that:

In an effort to reduce the overall time required in processing and granting Certificate of Correction requests, the Office will expedite processing and granting of patentee requests where such requests are accompanied by evidence to show that the error is attributable solely to the Office Where the correction requested was incurred through the

fault of the Office, and the matter is clearly disclosed in the records of the Office, and is accompanied by documentation that unequivocally supports the patentee's assertion(s), a Certificate of Correction will be expeditiously issued. MPEP § 1480.01

The following errors appear to have occurred through the fault of the Office, and the patentee respectfully requests correction thereof.

The Applicant filed a *Correction to Prior Information Disclosure Statement* on May 16, 2001 (received by OIPE May 18, 2001), a copy of which is attached. In the *Correction*, the Applicant corrected the page numbers for a non-patent literature reference, i.e. Hatalis et al., "High Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films", August 1987, pp. 361-364, IEEE Electron Device Letters, Vol. EDL-8, No. 8 (emphasis added). The corrected citation was included in an attached Form PTO-1449. Also, the *Correction* specifically included a request to "line through the incorrect reference and consider the corrected reference as indicated on the revised Form PTO-1449 submitted herewith" (emphasis added).

In response, the Examiner accepted this correction as noted in the Official Action mailed May 21, 2002, and evidenced by an initialed Form PTO-1449 attached to the Official Action, a copy of which is attached. However, the Examiner apparently overlooked the instruction to strike through the incorrect citation. Also, this oversight was not corrected by the Office when the application was prepared for issuance and publication as a patent.

As a result, there are two citations of the Hatalis article on the issued patent, only one of which is correct. Specifically, at page 3, column 2, under the heading "OTHER PUBLICATIONS," lines 3-6, the correct citation for the Hatalis article appears. However, at page 4, column 1, lines 26-29, an incorrect citation for the Hatalis article appears as "Hatalis et al., 'High Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films', Aug. 1987, pp. 161-164, IEEE Electron

Patent No. 7,067,844 Application Serial No. 09/832,844 Attorney Docket No. 0756-2288

Device Letters, vol. EDL-8, No. 8." (emphasis added). Since the second citation of the Hatalis article appears to have been included in the issued patent as the result of Patent Office error, the patentee respectfully requests that the issued patent be corrected by deleting the second citation of the Hatalis article at page 4, column 1, lines 26-29.

As the error was incurred through the fault of the Office, a fee is not believed to be necessary. Should it be determined that a fee is necessary, any deficiencies or overages in any fees due in connection with this patent and the requested actions should be applied to Deposit Account No. 50-2280(0756-2288).

Respectfully submitted,

Eric J. Robinson

Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C. PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789

(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO : 7,067,844

DATED : June 27, 2006

INVENTOR(S): Shunpei YAMAZAKI

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the "References Cited" section (56):

At page 4, column 1, lines 26-29, delete the following:

Hatalis et al., "High Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films", Aug. 1987, pp. 161-164, IEEE Electron Device Letters, vol. EDL-8, No. 8.

MAILING ADDRESS OF SENDER:

Eric J. Robinson
Robinson Intellectual Property Law Office
PMB 955
21010 Southbank Street
Potomac Falls, VA 20165

No. of additional copies

PATENT NO. 7,098,479

This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

ocket No.: 740756-2288 1765

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of: Shunpei YAMAZAKI) Art Unit: Unassigned Serial No.: 09/832,844) Examiner: Unassigned Filed: April 12, 2001 For: ELECTRO-OPTICAL DEVICE AND) METHOD FOR MANUFACTURING) THE SAME

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Posi with sufficient postage as First Class Mail in an envelope a Patents, Washington, D.C. 20231, on May 16, 2001.

CORRECTION TO PRIOR INFORMATION DISCLOSURE STATEMEN

Commissioner for Patents Washington, D.C. 20231

Sir:

In an "Information Disclosure Statement and Notification of Related Applications" filed April 12, 2001, Form PTO-1449 contained the following typographical errors:

U.S. Patent No. 4,849,797 was listed twice. Once correctly and once incorrectly as 4,894,797. It is requested that the Examiner line through the incorrect Patent, namely 4,894,797.

Japanese Laid-Open Patent No. 02-210330 was listed twice. Once correctly and once incorrectly as 02-120330. It is requested that that the Examiner line through the incorrect Patent, namely 02-120330.

Pages 361-364 of the IEEE Electron Device Letters "High Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films" written by Hatalis, were incorrectly cited as pages 161-164. Please line through the incorrect reference and consider the corrected reference as indicated on the revised Form PTO-1449 submitted herewith.

Copies of the above-mentioned references have already been provided and are not submitted herewith.

ocket No.: 740756-2288

The English Language Abstract of Japanese Laid-Open Patent No. 60-245174 was previously submitted with the aforementioned Information Disclosure Statement. Full English Translation of this reference is submitted herewith in accordance with 37 C.F.R. 1.98(a).

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the references listed on the attached Form PTO-1449 be made of record in the above-identified application.

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be required now or hereafter, or credit any overpayment to Deposit Account No. 19-2380.

Respectfully submitted,

Eric J. Robinson

Registration No. 38,285

NIXON PEABODY LLP 8180 Greensboro Drive, Suite 800 McLean, Virginia 22102 (703) 790-9110

MLT 60-245174 12/04/1985 JP Full Eng OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Examiner Initial MLT Hatalis et al., "High Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films", August 1987, pp. 361-364, IEEE Electron Device Letters, Vol. EDL-8, No. 8								
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